

a first etching step [of etching] to etch the first crystal layer through the first mask pattern;

a second growth step [of forming] to form a second crystal layer, the second crystal layer further having a surface, by growing a crystal of a III-V compound of the nitride system from the first crystal layer;

a second mask forming step [of forming] to form a second mask pattern on the surface of the second crystal layer;

a second etching step [of etching] to form the second crystal layer through the second mask pattern; and

a third growth step [of forming] to form a third crystal layer by growing a crystal of a III-V compound of the nitride system from the second crystal layer.

2. A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1,

further including:

between the second etching step and the third growth step, a step of removing at least part of the second mask pattern.

3. A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 2,

wherein the first mask pattern at least includes an under layer formed over the first crystal layer and an upper layer formed over the under layer.

4. A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 3,

wherein the upper layer of the first mask pattern, and the second mask pattern are formed of a material which can be dissolved by the same solution, and

the under layer of the first mask pattern is formed of a material which cannot be dissolved by the solution.

5. A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1,

wherein windows of the first mask pattern and windows of the second mask pattern do not overlie one another in the direction of the thickness of the crystal.

6. A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1,

wherein windows of the first mask pattern and windows of the second mask pattern at least in one place overlie one another in the direction of the thickness of the crystal, and at least in another place do not overlie one another in the direction of the thickness of the crystal.

7. A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1,

further including:

after the third growth step, a step of separating a portion of the crystal which includes at least the basal body, from the crystal.

8. A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1,

wherein an inner layer is formed at least in one of the first crystal layer, the second crystal layer and the third crystal layer, and the inner layer has a different composition from the crystal layer in which the inner layer is formed.

9. A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 8,

wherein the inner layer includes a III-V compound of the nitride system.

10. A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1,

wherein each of the first mask pattern and the second mask pattern includes a plurality of pattern elements arranged in one direction in a plane almost parallel to the surface of the basal body.

11. A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 10,

wherein both the pattern elements of the first mask pattern and the pattern elements of the second mask pattern are in the form of stripes.

12. A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1,

wherein each of the first mask pattern and the second mask pattern includes pattern elements arranged in two directions in a plane almost parallel to the surface of the basal body.

13. (Amended) A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1,

wherein each of the first mask pattern and the second mask pattern includes silicon (Si) and at least one element selected from the group consisting of oxygen (O) and nitrogen (N).

14. (Amended) A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 13,

wherein the basal body comprises at least one of a sapphire (Al_2O_3), silicon (Si), silicon carbide (SiC), gallium arsenide (GaAs), magnesium aluminum composite oxide (MgAl_2O_4), lithium gallium composite dioxide (LiGaO_2) and gallium nitride (GaN).

15. A method of manufacturing a device, the method including a crystal growth step of forming a crystal substrate or a crystal film and comprising manufacturing a device by forming a predetermined device film over the crystal substrate or the crystal film,

wherein the crystal growth step includes:

a first growth step of forming a first crystal layer by growing a crystal of a III-V compound of the nitride system on the surface of a basal body;

a first mask forming step of forming a first mask pattern on the surface of the first crystal layer;

a first etching step of etching the first crystal layer through the first mask pattern;

a second growth step of forming a second crystal layer by growing a crystal of a III-V compound of the nitride system from the first crystal layer;

a second mask forming step of forming a second mask pattern on the surface of the second crystal layer;

a second etching step of etching the second crystal layer through the second mask pattern; and

a third growth step of forming a third crystal layer by growing a crystal of a III-V compound of the nitride system from the second crystal layer.

16. A method of manufacturing a device as claimed in claim 15,
further including

a step of separating the basal body from the crystal substrate or the crystal film.

Remarks

Claims 1-30 were initially presented for prosecution. Due to a restriction requirement entered on 03 Dec., the applicant now elects claims 1 to 16 (corresponding to Group I - directed to method claims), and cancels claims 17-30. The applicant reserves the right to reintroduce claims 17-30 in this or subsequent applications.

Certain claims in Group I were also preliminarily amended to clear up any potential indefiniteness issues. The applicant states that the amendments were not narrowing amendments of any sort, were not made in response to cited prior art, were not made to overcome any prior art, and were not amended with the intent to surrender any subject matter. The reason for these amendments were simply to rectify clerical errors as they may arise.

The full group of claims 1 to 16 are rewritten here to expedite prosecution.